

Diodes

# Band switching diode

## 1SS390

●Applications

High frequency switching

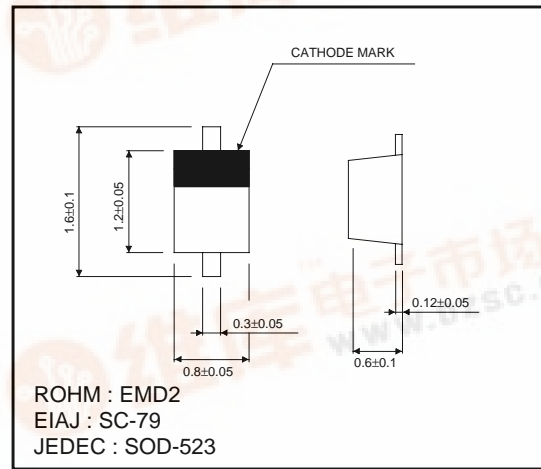
●Features

- 1) Extremely Small surface mounting type. (EMD2)
- 2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	35	V
DC forward current	$I_F$	100	mA
Junction temperature	$T_J$	125	°C
Storage temperature	$T_{stg}$	-55~+125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	1.0	V	$I_F=10mA$
Reverse current	$I_R$	-	-	10	nA	$V_R=25V$
Capacitance between terminals	$C_T$	-	-	1.2	pF	$V_R=6V, f=1MHz$
Forward operating resistance	$r_F$	-	-	0.9	$\Omega$	$I_F=2mA, f=100MHz$

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●Electrical characteristic curves (Ta=25°C)

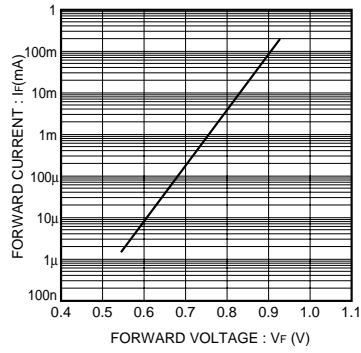


Fig. 1 Forward characteristics

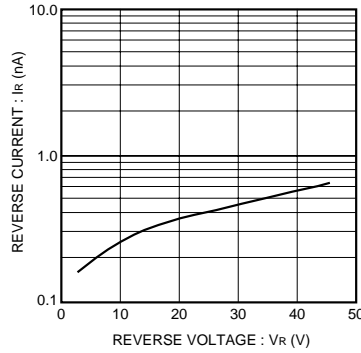


Fig. 2 Reverse characteristics

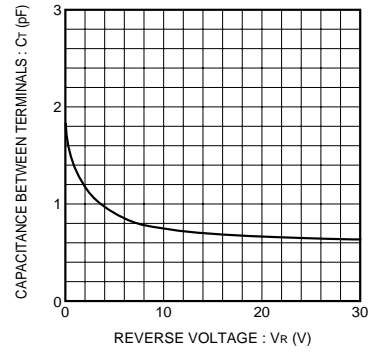


Fig. 3 Capacitance between terminals characteristics

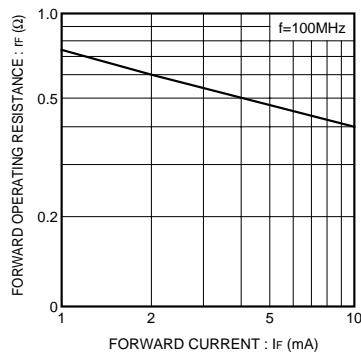


Fig. 4 Forward operating resistance characteristics